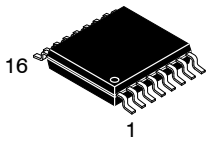
3.3 V, LVPECL/LVCMOS Clock Multiplier

NB3N3020



TSSOP−16
DT SUFFIX
CASE 948F

Description

The NB3N3020 is a high precision, low phase noise selectable clock multiplier. The device takes a 5 – 27 MHz fundamental mode parallel resonant crystal or a 2 – 210 MHz LVCMOS single ended clock source and generates a differential LVPECL output and a single ended LVCMOS/LVTTL output at a selectable clock output frequency which is a multiple of the input clock frequency. Three tri−level (Low, Mid, High) LVCMOS/LVTTL single ended select pins set one of 26 possible clock multipliers. The LVCMOS/LVTTL output enable (OE1) tri−states the LVCMOS/LVTTL clock output (CLK1) when low. When the LVTTL/LVCMOS output enable (OE2) is LOW, LVPECL CLK2 is forced LOW and LVPECL $\overline{CLK2}$ is forced HIGH.

This device is housed in 5 mm x 4.4 mm narrow body TSSOP 16 pin package.

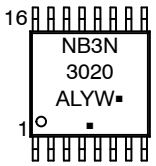
Features

- Selectable Clock Multiplier
- External Loop Filter is Not Required
- LVPECL Differential Output
- LVCMOS/ LVTTL Outputs
- RMS Period Jitter of 5 ps
- Jitter or Low Phase Noise at 125 MHz [25 MHz Input]:

Offset	Noise Power
100 Hz	−95 dBc/Hz
1 kHz	−107 dBc/Hz
10 kHz	−112 dBc/Hz
100 kHz	−117 dBc/Hz
1 MHz	−117 dBc/Hz
10 MHz	−134 dBc/Hz

- Operating Range 3.3 V ±10%
- Industrial Temperature Range −40°C to +85°C
- These are Pb−Free Devices

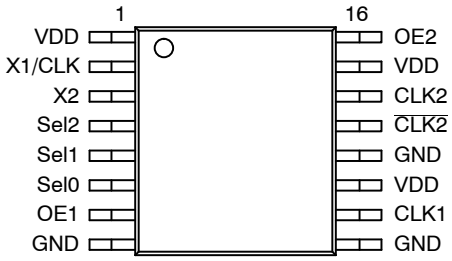
MARKING DIAGRAM



A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
▪	= Pb−Free Package

(Note: Microdot may be in either location)

PIN CONFIGURATION



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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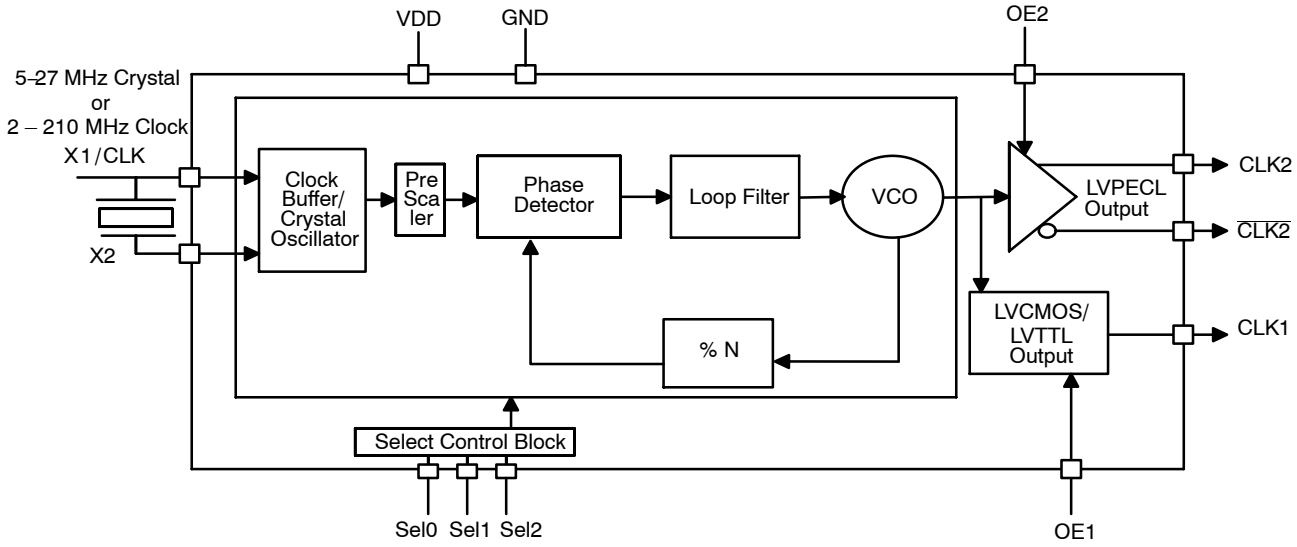


Figure 1. NB3N3020 Simplified Logic Diagram

Table 1. PIN DESCRIPTION

Pin	Name	I/O	Description
6	Sel0	Tri−Level Input	Frequency select input 0. When left open, defaults to VDD/ 2. See output select Table 2 for details.
5	Sel1	Tri−Level Input	Frequency select input 1. When left open, defaults to VDD/ 2. See output select Table 2 for details.
4	Sel2	Tri−Level Input	Frequency select input 2. When left open, defaults to VDD/ 2. See output select Table 2 for details.
1, 11, 15	V_{DD}	Power Supply	Positive supply voltage pins are connected to +3.3 V supply voltage.
2	X1/CLK	Input	Crystal or Clock input. Connect to 5 − 27 MHz crystal source or 2 − 210 MHz single−ended clock. See Table 2.
3	X2	Input	Crystal input. Connect to a 5 − 27 MHz crystal or leave unconnected for clock input. See Table 2.
7	OE1	LVTTL/LVCMOS Input	Output enable input that synchronously tri−states CLK1 output when low. Internal pull−up resistor to V_{DD}.
16	OE2	LVTTL/LVCMOS Input	Output enable input that when LOW synchronously controls LVPECL outputs by forcing CLK2 LOW and $\overline{CLK2}$ HIGH. Internal pull−up resistor to V_{DD}.
8, 9, 12	GND	Power Supply	Ground 0 V. These pins provide GND return path for the devices.
13	$\overline{CLK2}$	LVPECL Output	Inverted clock output. Clock frequency equals input frequency times multiplier.
14	CLK2	LVPECL Output	Non−inverted clock output. Clock frequency equals input frequency times multiplier.
10	CLK1	LVTTL/ LVCMOS Output	Clock Output. Clock frequency equals input frequency times multiplier.

Table 2. OUTPUT FREQUENCY CLOCK MULTIPLIER SELECT TABLE

Sel2	Sel1	Sel0	CLK1, CLK2, $\overline{CLK2}$	Clock Input Range [MHz]	Crystal Input Range [MHz]
L	L	L	Low (Power Down)	–	–
L	L	M	Input X 1	25 – 210	25 – 27
L	L	H	Input X 4/3 (or 1 1/3)	15 –157.5	15 – 27
L	M	L	Input X 1.5	10 – 140	10 – 27
L	M	M	1.6	25 – 131.25	25 – 27
L	M	H	Input X 1.875	40 – 112	–
L	H	L	Input X 2	25 – 105	25 – 27
L	H	M	Input X 7/3 (or 2 1/3)	15 – 90	15 – 27
L	H	H	Input X 2.4	25 – 87.5	25 – 27
M	L	L	Input X 2.5	10 – 84	10 – 27
M	L	M	Input X 8/3 (or 2 2/3)	15 – 78.75	15 – 27
M	L	H	Input X 3	15 – 70	15 – 27
M	M	L	Input X 3.125	40 – 67.20	–
M	M	M	Input X 3.2	25 – 65.63	25 – 27
M	M	H	Input X 10/3 (or 3 1/3)	15 – 63	15 – 27
M	H	L	Input X 3.75	20 – 56	20 – 27
M	H	M	Input X 4	2 – 52.5	5 – 25
M	H	H	Input X 5	6 – 42	6 – 27
H	L	L	Input X 6	5 – 35	5 – 27
H	L	M	Input X 6.25	20 – 33.6	20 – 27
H	L	H	Input X 19/3 (or 6 1/3)	15 – 33.16	15 – 27
H	M	L	Input X 8	5 – 26.25	5 – 26.25
H	M	M	Input X 25/3 (or 8 1/3)	15 – 25.2	15 – 25.2
H	M	H	Input X 10	5 – 21	5 – 21
H	H	L	Input X 12	5 – 17.5	5 – 17.5
H	H	M	Input X 12.5	10 – 16.8	10 – 16.8
H	H	H	Input X 16	5 – 13.125	5 – 13.125

L – Low, M – Mid, H – High

Recommended Crystal Parameters

Crystal	Fundamental AT−Cut
Frequency	5 – 27 MHz
Load Capacitance	16 – 20 pF
Shunt Capacitance, C0	7 pF Max
Equivalent Series Resistance	35 Ω Max
Initial Accuracy at 25°C	±20 ppm
Temperature Stability	±30 ppm
Aging	±20 ppm
C0/C1 Ration	250 Max

Device Operation

The NB3N3020 is a Clock multiplier. The device can take crystal or clock input and generates LVPECL and LVCMOS/ LVTTL clock outputs which are multiples of the input as determined by the tri−level select inputs [Sel0, Sel1, Sel2].

Clock Multiplication

NB3N3020 is a clock multiplier with the clock multiplier selected by the tri level select inputs [Sel0, Sel1, Sel2]. NB3N3020 has a LVTTL/LVCMOS output [CLK1] and a LVPECL clock output [CLK2, $\overline{CLK2}$].

Output Enable

The device has an output enable [OE] which is used to tri−state the outputs. OE1 controls the CLK1 clock output where as OE2 controls the CLK2, $\overline{CLK2}$ clock outputs. When OE1or OE2 are disabled, the respective clock output(s) are tri−stated. In this mode of operation, PLL is still running, with the respective clock outputs tri−stated. When the OE1 or OE2 are enabled, the clock outputs

become active synchronous to the internal PLL output clock and do not create any glitches or runt pulses during the transition. In power down mode, the outputs are tri−stated regardless of the state of the OE1, OE2.

The device has an output enable [OE1] which accepts LVTTL/LVCMOS levels and when set LOW will disable the LVTTL/LVCMOS level CLK1 to tri − state. Output enable OE2 accepts LVTTL/LVCMOS levels to disable the LVPECL level outputs by forcing CLK2 LOW and CLK2b HIGH. When OE1 or OE2 are set LOW (Disabled), the PLL remains running while the respective clock outputs are disabled. When the OE1 or OE2 are set enabled (HIGH), the clock outputs become active synchronous to the internal PLL output clock and will not create any glitches or runt pulses during the transition. Both OE1 and OE2 inputs have pull−up resistors which default to VDD when floated open. In power down mode, the outputs are tri − stated (zero current) regardless of the state of the OE1, OE2.

Changing Clock Multiplier

The clock output frequency can be dynamically changed using Sel0, Sel1, Sel2 pins. When the clock frequency is changed, the clock outputs move from one frequency to another and the PLL locks to the new frequency within a settling time of 3 msec. There is no glitch during this transition when the clock outputs are active {not tri−stated by OE1, OE2}.

Crystal/ Clock Input

The device takes in a 5 – 27 MHz crystal input or 2 – 210 MHz clock input. Once powered up, the input frequency is fixed and should not be changed dynamically. The input cannot accept a spread spectrum clock and needs a fixed frequency clock for device operation. The input frequencies for clock and crystal input for specific multipliers are determined by Table 3.

Power Up

When the NB3N3020 is powered up, it takes 10 msec for the PLL's to stabilize and lock to the desired frequency of operation as selected by Sel0, Sel1, Sel2. During this time period, there may be glitches in the clock outputs.

Power Down:

The device can be powered down when the Sel0, Sel1, Sel2 pins are all connected to GND. In this mode of operation, PLL is turned off and the device consumes less than 5 mA of current. There may be a glitch in clock outputs when the device is powering down. In power down mode, the outputs are tri−stated regardless of the state of the OE1, OE2.

In the cases where the application requires glitch−less transitions, in order to avoid glitches it is recommended to use synchronous OE signaling to mask glitches to the clock outputs.

Table 3. ATTRIBUTES

Characteristics		Value
ESD Protection	Human Body Model	2 kV
Moisture Sensitivity, Indefinite Time Out of Dry pack (Note 1)		Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in
Transistor Count		8287 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

1. For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS (Note 2)

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{DD}	Positive Power Supply	GND = 0 V		4.6	V
V_I	Input Voltage (VIN)	GND = 0 V	$GND \le V_I \le V_{DD}$	−0.5 V to V_{DD} + 0.5 V	V
I_{out}	LVPECL Output Current	Continuous Surge		25 50	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	TSSOP−16 TSSOP−16	138 108	°C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	(Note 3)	TSSOP−16	33 to 36	°C/W
T_{sol}	Wave Solder			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and not valid simultaneously. If stress limits are exceeded device functional operation is not implied, damage may occur and reliability may be affected.
3. JEDEC standard multilayer board − 2S2P (2 signal, 2 power).

Table 5. DC CHARACTERISTICS (V_{DD} = 3.3 V ±10%, GND = 0 V, T_A = −40°C to +85°C)

Symbol	Characteristic	Min	Typ	Max	Unit
V_{DD}	Power Supply Voltage	2.97	3.3	3.63	V
I_{DD}	Power Supply Current (Note 4)		60	75	mA
I_{DDOE}	Power Supply Current when OE1, OE2 is Set Low		50		mA
I_{DDOFF}	Power Supply Current when PLL is powered off by Sel0, Sel1, Sel2			5	mA
V_{IH}	Input HIGH Voltage (X1/CLK, OE1, OE2)	2000		V_{DD} + 300	mV
V_{IL}	Input LOW Voltage (X1/$\overline{CLK}$, OE1, OE2)	GND − 300		800	mV
V_{IH}	Input HIGH Voltage (Sel0, Sel1, Sel2)	0.72 V_{DD}		V_{DD} + 300	mV
V_{IL}	Input LOW Voltage (Sel0, Sel1, Sel2)	GND − 300		800	mV
V_{IM}	Input Mid Voltage (Sel0, Sel1, Sel2) (When left open, defaults to $V_{DD}/2$		$V_{DD}/2$		mV
V_{OH}	Output HIGH Voltage for CLK2, $\overline{CLK2}$ (See Figure 3)	V_{DD} − 1.145		V_{DD} − 0.895	V
V_{OL}	Output LOW Voltage for CLK2, $\overline{CLK2}$ (See Figure 3)	V_{DD} − 2.090		V_{DD} − 1.600	V
V_{OH}	Output HIGH Voltage for CLK1 [I_{OH} = −12 mA]	2.4			V
V_{OL}	Output LOW Voltage for CLK1 [I_{OL} = 12 mA]			0.4	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. Measurement taken at $FCLK_{out}$ = 125 MHz with LVPECL and LVCMOS/ LVTTL outputs not terminated.

Table 6. AC CHARACTERISTICS (V_{DD} = 3.3 V ±10%, GND = 0 V, T_A = −40°C to +85°C) (Note 5)

Symbol	Characteristic	Min	Typ	Max	Unit
f_{CLKIN}	Crystal Input Frequency	5.0		27	MHz
f_{CLKIN}	Clock Input Frequency	2.0		210	MHz
f_{CLKOUT}	Output Clock Frequency			210	MHz
Φ_{NOISE}	Phase−Noise Performance (f_{CLKout} = 125 MHz, 25 MHz input)				
	@ 100 Hz offset from carrier		−95		dBc/Hz
	@ 1 kHz offset from carrier		−107		dBc/Hz
	@ 10 kHz offset from carrier		−112		dBc/Hz
	@ 100 kHz offset from carrier		−117		dBc/Hz
	@ 1 MHz offset from carrier		−117		dBc/Hz
	@ 10 MHz offset from carrier		−134		dBc/Hz
Tjitter p−p	Cycle−to−Cycle Jitter peak to peak (Note 6) f_{CLKout} = 100 MHz and 125 MHz, 25 MHz input		20	36	ps
Tjitter rms	Cycle−to−Cycle Jitter rms (Note 7) f_{CLKout} = 100 Mhz and 125 MHz, 25 MHz input		5.0	9.0	ps
Tjitter p−p	Period Jitter peak to peak (Note 7) f_{CLKout} = 100 MHz and 125 MHz, 25 MHz input		15	20	ps
Tjitter rms	Period Jitter rms (Note 7) f_{CLKout} = 100 MHz and 125 MHz, 25 MHz input		3.0	5.0	ps
	Start up time from power up		10		ms
OE	Output Enable/Disable Time		10		us
	PLL settling time		3		ms
t_{DUTY_CYCLE}	Output Clock Duty Cycle (Measured at cross point for LV PECL clock output and VDD/2 for LVCMOS/ LVTTL clock output)	45	50	55	%
t_R	Output Rise Time (Note 5) (Measured from 20% to 80%. Figure 2) LV PECL Output		340	700	ps
t_F	Output Fall Time (Note 5) (Measured from 20% to 80%. Figure 2) LV PECL Output		340	700	ps
t_R	Output Rise Time (Measured from 0.8 to 2 V, no load) LVCMOS/ LV TTL Output			1500	ps
t_F	Output Fall Time (Measured from 2.0 V to 0.8 V, no load) LVCMOS/ LV TTL Output			1500	ps
t_R/ t_F	Input Rise time/ Fall time for LV CMOS/ LV TTL clock input [X1/CLK]	0		1500	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

5. Measurement taken with outputs terminated with 50 Ω to V_{DD} − 2 V. See Figure 2.
6. Sampled with 1000 cycles
7. Sampled with 10000 cycles

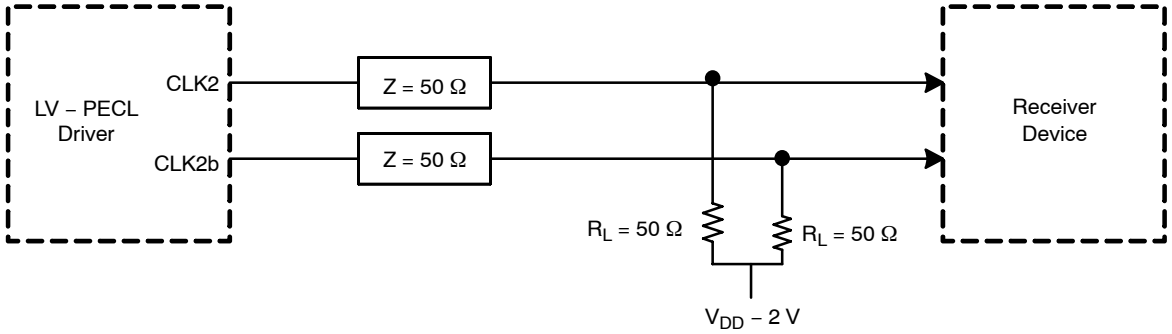


Figure 2. Typical Termination for Output Driver for Device Evaluation

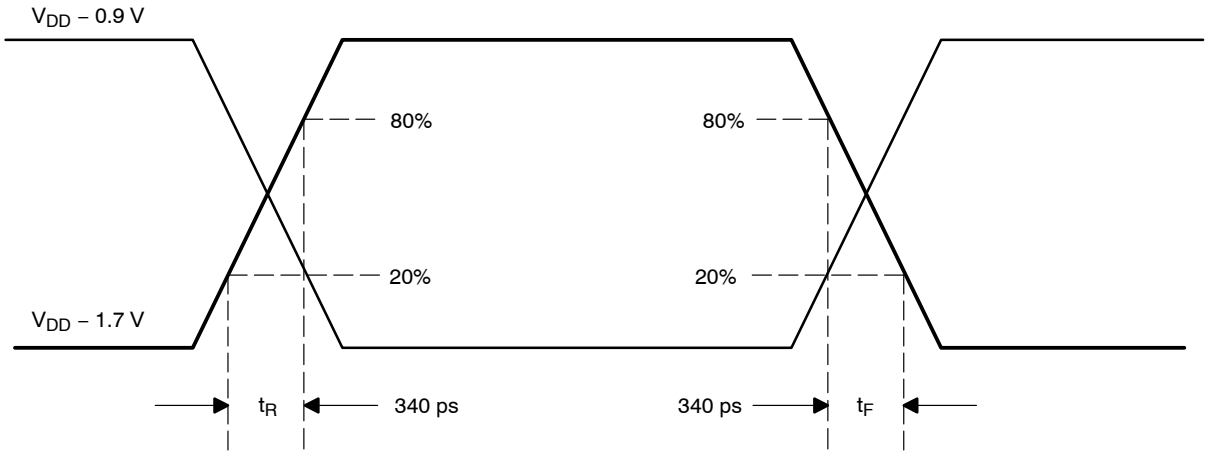
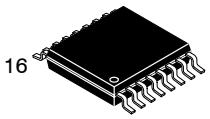


Figure 3. LV−PECL Output Parameter Characteristics

ORDERING INFORMATION

Device	Package	Shipping†
NB3N3020DTG	TSSOP−16 (Pb−Free)	96 Units / Rail
NB3N3020DTR2G	TSSOP−16 (Pb−Free)	2500 / Tape & Reel

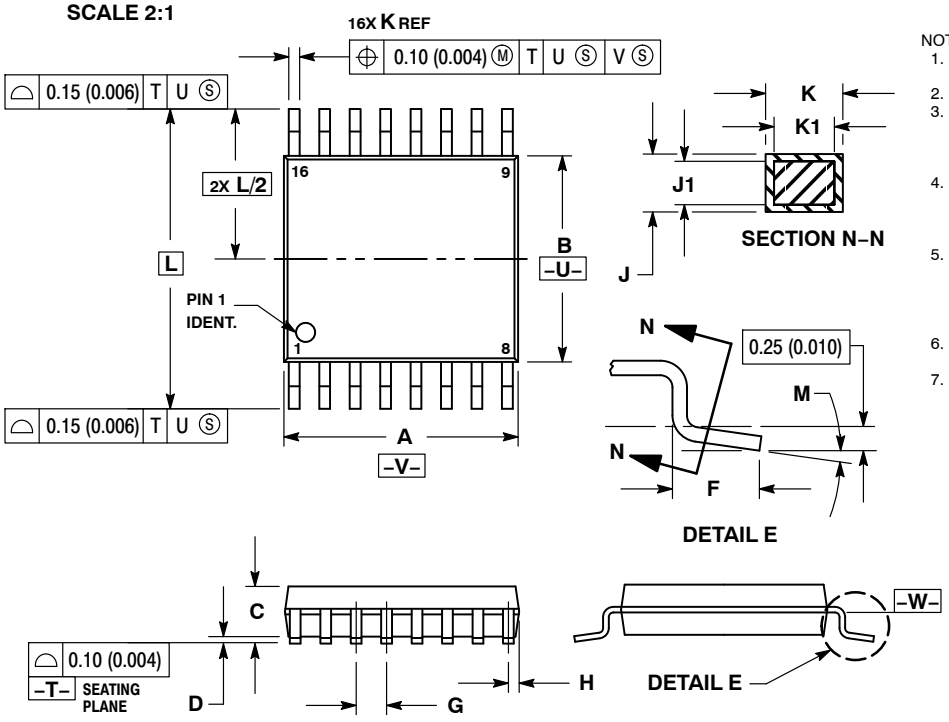
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 2:1

TSSOP−16 WB
CASE 948F
ISSUE B

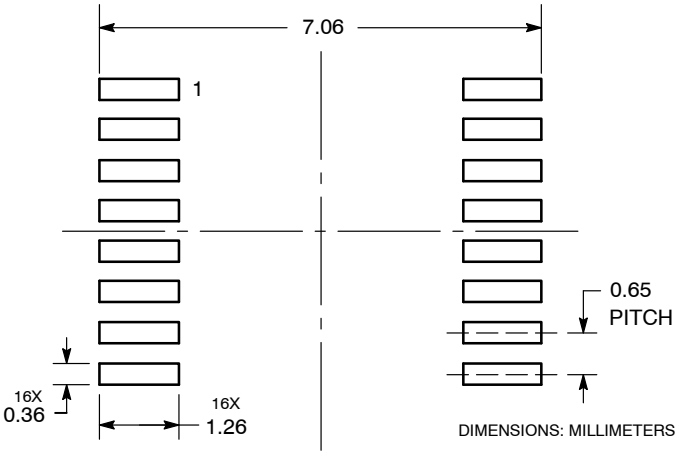
DATE 19 OCT 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

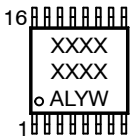
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
G or ▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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